



Attorney's Docket No.: 10559-880001/P17482
Intel Corporation

IEW

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Applicant : Yan Borodovsky
Serial No.: 10/688,337
Filed : October 17, 2003
Assignee : Intel Corporation
Title : COMPOSITE PATTERNING WITH TRENCHES

Art Unit: 1765
Examiner:

Mail Stop Amendment

Commissioner for Patents
P.O. Box 1450
Alexandria, VA 22313-1450

INFORMATION DISCLOSURE STATEMENT

Dear Sir:

Applicants call attention to the attached Information Disclosure Statement and documents listed on form PTO-1449.

This filing is being made before the receipt of a first Office action on the merits. No fee is required.

The documents are in the English language; hence no concise explanation is necessary per Rule 98(a)(3).

Consideration of the foregoing and enclosures plus the return of a copy of the enclosed form PTO-1449 with the

CERTIFICATE OF MAILING BY FIRST CLASS MAIL

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March 29, 2005

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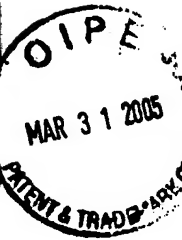
Signature

Jennifer H. Payne

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Applicant : Yan Borodovsky
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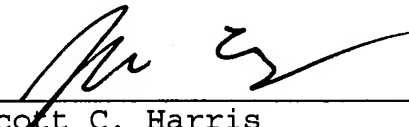


Examiner's initials in the left column per MPEP 609 are earnestly solicited along with an early action on the merits.

Please apply any additional charges or credits to Deposit Account No. 06-1050.

Respectfully submitted,

Date: March 29, 2005

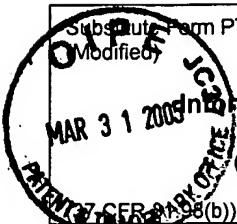


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 Substitute Form PTO-1449 Modified	U.S. Department of Commerce Patent and Trademark Office		Attorney's Docket No. 10559-880001	Application No. 10/688,337
	Information Disclosure Statement by Applicant (Use several sheets if necessary)			
	Applicant Yan Borodovsky		Filing Date October 17, 2003	Group Art Unit 1765

U.S. Patent Documents

Examiner Initial	Desig. ID	Document Number	Publication Date	Patentee	Class	Subclass	Filing Date If Appropriate
	AA						
	AB						
	AC						
	AD						

Foreign Patent Documents or Published Foreign Patent Applications

Examiner Initial	Desig. ID	Document Number	Publication Date	Country or Patent Office	Class	Subclass	Translation	
							Yes	No
	AE							
	AF							
	AG							

Other Documents (include Author, Title, Date, and Place of Publication)

Examiner Initial	Desig. ID	Document
	AH	M. Fritze, et al., "Gratings of regular arrays and trim exposures for ultralarge scale integrated circuit phase-shift lithography", <i>J. of Vacuum Science & Technology B</i> , 19(6):2366-2370, Nov/Dec 2001.
	AI	J.A. Hoffnagle, et al., "Liquid immersion deep-ultraviolet interferometric lithography", <i>J. of Vacuum Science & Technology B</i> , 17(6):3306-3309, Nov/Dec 1999.
	AJ	Marc D. Levenson, et al., "Exposing the DUV SCAAM - 75 nm Imaging on the Cheap!", <i>Proc. of SPIE: Design, Process Integration, and Characterization for Microelectronics</i> , 4692:288-297, March 2002.
	AK	Alex K. Raub, et al., "Deep UV immersion interferometric lithography", <i>Proc. of SPIE: Optical Microlithography XVI</i> , 5040:667-678, Feb. 2003.
	AL	Bruce W. Smith, et al., "Water immersion optical lithography at 193 nm", <i>J. Microlith., Microfab., Microsyst.</i> , 3(1):44-51, Jan. 2004.
	AM	Akiyoshi Susuki, et al., "Multilevel imaging system realizing $k_1 \pm 0.3$ lithography", <i>Proc. of SPIE: Optical Microlithography XII</i> , 3679:396-407, Mar. 1999.
	AN	M. Switkes, et al., "Extending optics to 50 nm and beyond with immersion lithography", <i>J. of Vacuum Science & Technology B</i> , 21(6):2794-2799, Nov/Dec 2003.
	AO	Brian Tyrrell, et al., "Investigation of the physical and practical limits of dense-only phase shift lithography for circuit feature definition", <i>J. Microlith., Microfab., Microsyst.</i> , 1(3):244-252, Oct. 2002.
	AP	Saleem H. Zaidi, et al., "Multiple exposure interferometric lithography", <i>Proc. of SPIE: Optical Microlithography VII</i> , 2197:869-875, Mar. 1994.
	AQ	M. Fritze, et al., "Preprint of poster presentation entitled "High-Throughput Hybrid Optical Maskless Lithography: All-Optical 32-nm Node Imaging," Presented at SPIE Microlithography 2005, San Jose, California, USA, March 3, 2005.

Examiner Signature	Date Considered
EXAMINER: Initials citation considered. Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	